



DMG2302U

N-CHANNEL ENHANCEMENT MODE MOSFET

Features

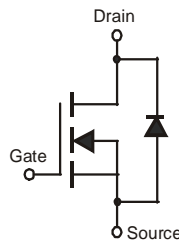
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

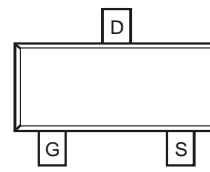
- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)



TOP VIEW



Internal Schematic



TOP VIEW

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	± 8	V
Continuous Drain Current (Note 3)	Steady State	$T_A = 25^\circ\text{C}$	I_D	4.2	A
		$T_A = 70^\circ\text{C}$		3.4	
Pulsed Drain Current (Note 4)			I_{DM}	27	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 3)	$T_A = 25^\circ\text{C}$	P_D	0.8	W
	$T_A = 70^\circ\text{C}$		0.5	
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ\text{C}$		$R_{\theta JA}$	156	$^\circ\text{C/W}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. No purposefully added lead.
 2. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 3. Repetitive rating, pulse width limited by junction temperature.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current $T_J = 25^\circ\text{C}$	I_{DSS}	-	-	1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(th)}$	0.4	-	1.0	V	$V_{DS} = V_{GS}, I_D = 50\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	-	-	90	m Ω	$V_{GS} = 4.5V, I_D = 3.6A$
				120		$V_{GS} = 2.5V, I_D = 3.1A$
Forward Transfer Admittance	$ Y_{fs} $	-	13	-	S	$V_{DS} = 5V, I_D = 3.6A$
Diode Forward Voltage	V_{SD}	-	0.75	1.0	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C_{iss}	-	594.3	-	pF	$V_{DS} = 10V, V_{GS} = 0V,$ $f = 1.0MHz$
Output Capacitance	C_{oss}	-	64.5	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	57.7	-	pF	
Gate Resistance	R_g	-	1.5	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Q_g	-	7.0	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_D = 3.6A$
Gate-Source Charge	Q_{gs}	-	0.9	-	nC	
Gate-Drain Charge	Q_{gd}	-	1.4	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	7.4	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$ $R_L = 2.78\Omega, R_G = 1.0\Omega$
Turn-On Rise Time	t_r	-	9.8	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	28.1	-	ns	
Turn-Off Fall Time	t_f	-	6.7	-	ns	

Notes: 4. Short duration pulse test used to minimize self-heating effect.
5. Guaranteed by design. Not subject to production testing.